

SOD-323 Plastic-Encapsulate Diode

PRODUCT SUMMARY

RB551V-30 Schottky Diodes

FEATURES

High current rectifier Schottky diode Low voltage, low inductance For power supply

MARKING: D



Po Pb-free; RoHS-compliant



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Single Diode @ T_A = 25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	V	
DC reverse voltage	V _R	20	V
Mean rectifying current	Io	0.5	А
Peak forward surge current	I _{FSM}	2	А
Junction temperature	Tj	125	℃
Storage temperature	T _{stg}	-40~+125	$^{\circ}$

ELECTRICAL RATINGS

@ $T_A = 25^{\circ}C$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V _F			0.36	, ,	I _F =100mA
				0.47	V	I _F =500mA
Reverse current	I _R			100	μΑ	V _R =20V



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TYPICAL CHARACTERISTICS

Electrical Characteristic curves (T_a = 25°C)

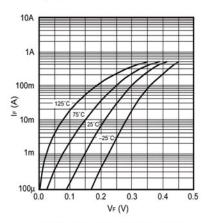


Fig.1 Forward characteristics

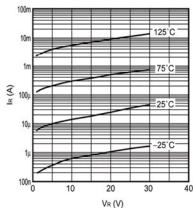


Fig.2 Reverse characteristics

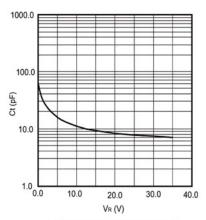


Fig.3 Capacitance between terminals characteristics

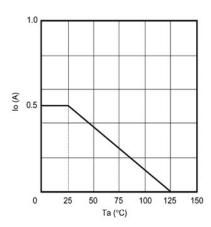


Fig.4 Derating curve

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